HSP45240/883

February 1998

Address Sequencer

Features

- **This Circuit is Processed in Accordance to MIL-STD-883 and is Fully Conformant Under the Provisions of Paragraph 1.2.1.**
- **Block Oriented 24-Bit Sequencer**
- **Configurable as Two Independent 12-Bit Sequencers**
- **24 x 24 Crosspoint Switch**
- **Programmable Delay on 12 Outputs 9-**
- **Multi-Chip Synchronization Signals**
- **Standard µP Interface**
- **100pF Drive on Outputs**
- **DC to 40MHz Clock Rate**

Applications

- **1-D, 2-D Filtering**
- **Pan/Zoom Addressing**
- **FFT Processing**
- **Matrix Math Operations**

Ordering Information

PART NUMBER	TEMP. RANGE (^{O}C)	PACKAGE	PKG. NO.
HSP45240GM-25/883	-55 to 125	68 Ld PGA	
HSP45240GM-33/883	-55 to 125	68 Ld PGA	
HSP45240GM-40/883	-55 to 125	68 Ld PGA	

Description

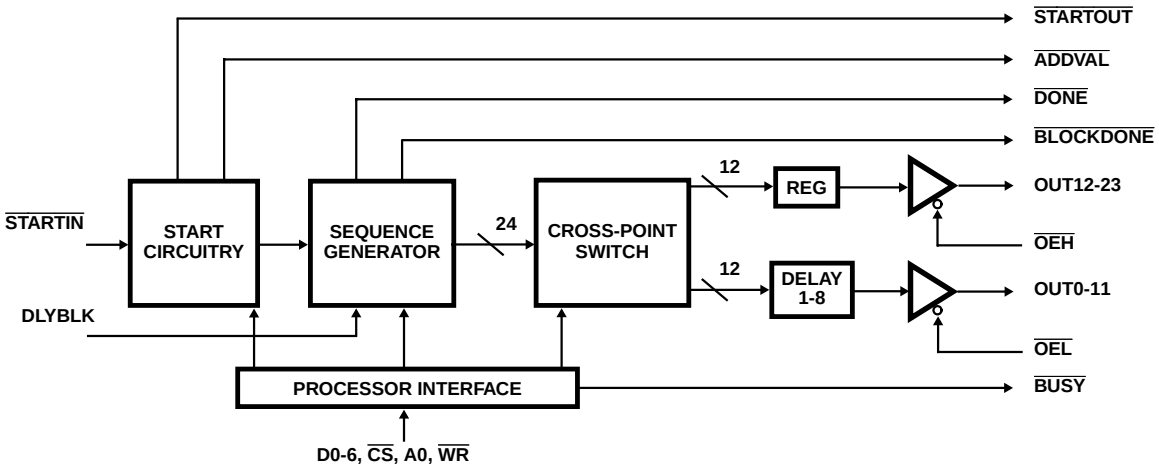
The Intersil HSP45240/883 is a high speed Address Sequencer which provides specialized addressing for functions like FFTs, 1-D and 2-D filtering, matrix operations, and image manipulation. The sequencer supports block oriented addressing of large data sets up to 24 bits at clock speeds up to 40MHz.

Specialized addressing requirements are met by using the onboard 24 x 24 crosspoint switch. This feature allows the mapping of the 24 address bits at the output of the address generator to the 24 address outputs of the chip. As a result, bit reverse addressing, such as that used in FFTs, is made possible.

A single chip solution to read/write addressing is also made possible by configuring the HSP45240 as two 12-bit sequencers. To compensate for system pipeline delay, a programmable delay is provided on 12 of the address outputs.

The HSP45240 is manufactured using an advanced CMOS process, and is a low power fully static design. The configuration of the device is controlled through a standard microprocessor interface and all inputs/outputs, with the exception of clock, are TTL compatible.

Block Diagram



CAUTION: These devices are sensitive to electrostatic discharge; follow proper IC Handling Procedures.

File Number **2816.3**

Absolute Maximum Ratings

Supply Voltage . . . . . +8.0V
Input, Output Voltage Applied. . . . . GND -0.5V to V_{CC} +0.5V
ESD Classification . . . . . Class 1

Operating Conditions

Temperature Range . . . . . -55^{o}C to 125^{o}C
Voltage Range . . . . . +4.5V to +5.5V

Thermal Information

Thermal Resistance (Typical, Note 1)	θ_{JA} (^{o}C/W)	θ_{JC} (^{o}C/W)
PGA Package	37.1	10.1

Maximum Package Power Dissipation at 125^{o}C
PGA Package 1.35W
Maximum Junction Temperature . . . . . 175^{o}C
Maximum Storage Temperature Range . . . . . -65^{o}C to 150^{o}C
Maximum Lead Temperature (Soldering 10s) . . . . . 300^{o}C

Die Characteristics

Gate Count 8,388

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

TABLE 1. DC ELECTRICAL SPECIFICATIONS

Device Guaranteed and 100% Tested

PARAMETER	SYMBOL	TEST CONDITIONS	GROUP A SUB-GROUPS	TEMPERATURE (^{o}C)	LIMITS		UNITS
					MIN	MAX	
Logical One Input Voltage	V_{IH}	V_{DD} = 5.5V	1, 2, 3	-55 ≤ T_A ≤ 125	2.2	-	V
Logical Zero Input Voltage	V_{IL}	V_{DD} = 4.5V	1, 2, 3	-55 ≤ T_A ≤ 125	-	0.8	V
Output HIGH Voltage	V_{OH}	I_{OH} = -400µA V_{DD} = 4.5V (Note 2)	1, 2, 3	-55 ≤ T_A ≤ 125	2.6	-	V
Output LOW Voltage	V_{OL}	I_{OL} = +2.0mA V_{CC} = 4.5V (Note 2)	1, 2, 3	-55 ≤ T_A ≤ 125	-	0.4	V
Input Leakage Current	I_I	V_{IN} = V_{CC} or GND V_{CC} = 5.5V	1, 2, 3	-55 ≤ T_A ≤ 125	-10	+10	µA
Output Leakage Current	I_O	V_{OUT} = V_{CC} or GND V_{CC} = 5.5V	1, 2, 3	-55 ≤ T_A ≤ 125	-10	+10	µA
Clock Input High	V_{IHC}	V_{CC} = 5.5V	1, 2, 3	-55 ≤ T_A ≤ 125	3.0	-	V
Clock Input Low	V_{ILC}	V_{CC} = 4.5V	1, 2, 3	-55 ≤ T_A ≤ 125	-	0.8	V
Standby Power Supply Current	I_{CCSB}	V_{IN} = V_{CC} or GND V_{CC} = 5.5V, Outputs Open	1, 2, 3	-55 ≤ T_A ≤ 125	-	500	µA
Operating Power Supply Current	I_{CCOP}	f = 33MHz V_{CC} = 5.5V (Note 3)	1, 2, 3	-55 ≤ T_A ≤ 125	-	99	mA
Functional Test	FT	(Note 4)	7, 8	-55 ≤ T_A ≤ 125	-	-	

NOTES:

2. Interchanging of force and sense conditions is permitted.
3. Operating Supply Current is proportional to frequency, typical rating is 3mA/MHz.
4. Tested as follows: t = 1MHz, V_{IH} = 2.6, V_{IL} = 0.4, V_{OH} ≥ 1.5V, V_{OL} ≤1.5V, V_{IHC} = 3.4V, and V_{ILC} = 0.4V.

TABLE 2. AC ELECTRICAL SPECIFICATIONS

Device Guaranteed and 100% Tested

PARAMETER	SYMBOL	GROUP A SUBGROUP	TEMPERATURE (^oC)	-25 (25MHz)		-33 (33MHz)		-40 (40MHz)		UNITS
				MIN	MAX	MIN	MAX	MIN	MAX	
Clock Period	t_{CP}	9, 10, 11	$-55 \le T_A \le 125$	39	-	30	-	25	-	ns
Clock Pulse Width High	t_{CH}	9, 10, 11	$-55 \le T_A \le 125$	15	-	12	-	10	-	ns
Clock Pulse Width Low	t_{CL}	9, 10, 11	$-55 \le T_A \le 125$	15	-	12	-	10	-	ns
Setup Time D0-6 to $\overline{WR}$ High	t_{DS}	9, 10, 11	$-55 \le T_A \le 125$	17	-	16	-	14	-	ns
Hold Time D0-6 from $\overline{WR}$ Low	t_{DH}	9, 10, 11	$-55 \le T_A \le 125$	0	-	0	-	0	-	ns
Setup Time A, $\overline{CS}$ to $\overline{WR}$ Low	t_{AS}	9, 10, 11	$-55 \le T_A \le 125$	5	-	5	-	5	-	ns
Hold Time A, $\overline{CS}$ from $\overline{WR}$ High	t_{AH}	9, 10, 11	$-55 \le T_A \le 125$	0	-	0	-	0	-	ns
Pulse Width for $\overline{WR}$ Low	t_{WRL}	9, 10, 11	$-55 \le T_A \le 125$	18	-	14	-	12	-	ns
Pulse Width for $\overline{WR}$ High	t_{WRH}	9, 10, 11	$-55 \le T_A \le 125$	18	-	14	-	12	-	ns
$\overline{WR}$ Cycle Time	t_{WP}	9,10,11	$-55 \le T_A \le 125$	39	-	30	-	25	-	ns
Set-up Time $\overline{STARTIN}$, DLYBLK, to Clock High	t_{IS}	9, 10, 11	$-55 \le T_A \le 125$	15	-	12	-	10	-	ns
Hold Time $\overline{STARTIN}$, DLYBLK, to Clock High	t_{IH}	9, 10, 11	$-55 \le T_A \le 125$	0	-	0	-	0	-	ns
Clock to Output Prop. Delay on OUT0-23	t_{PDO}	9, 10, 11	$-55 \le T_A \le 125$	-	18	-	16	-	14	ns
Clock to Prop. Delay, on $\overline{STARTOUT}$, $\overline{BLKDONE}$, $\overline{DONE}$, $\overline{ADVAL}$, and $\overline{BUSY}$	t_{PDS}	9, 10, 11	$-55 \le T_A \le 125$	-	18	-	16	-	14	ns
Output Enable Time (Note 6)	t_{EN}	9, 10, 11	$-55 \le T_A \le 125$	-	22	-	20	-	15	ns
$\overline{RST}$ Low Time	t_{RST}	9, 10, 11	$-55 \le T_A \le 125$	2 Clock Cycles						ns

NOTES:

5. AC Testing: V_{CC} = 4.5V and 5.5V, inputs are driven at 3.0V for Logic “1” and 0.0V for a Logic “0”. Input and output timing measurements are made at 1.5V for both a logic “1” and “‘0”. CLK is driven at 4.0V and 0V and measured at 2.0V.
6. Transition is measured at ±200mV from steady state voltage with loading as specified by test load circuit and C_L = 40pF.

TABLE 3. ELECTRICAL PERFORMANCE SPECIFICATIONS

PARAMETERS	SYMBOL	TEST CONDITIONS	NOTES	TEMPERATURE	-25 (25MHz)		-33 (33MHz)		-40 (40MHz)		UNITS
					MIN	MAX	MIN	MAX	MIN	MAX	
Input Capacitance	C_{IN}	V_{CC} = Open, f = 1MHz, All measurements are referenced to device GND.	7	T_A = 25	-	10	-	10	-	10	pF
Output Capacitance	C_{OUT}	V_{CC} = Open, f = 1MHz, All measurements are referenced to device GND.	7	T_A = 25	-	10	-	10	-	10	pF
Output Disable	t_{OEZ}		7, 8	$-55 \le T_A \le 125$	-	22	-	20	-	15	ns

TABLE 3. ELECTRICAL PERFORMANCE SPECIFICATIONS (Continued)

PARAMETERS	SYMBOL	TEST CONDITIONS	NOTES	TEMPERATURE	-25 (25MHz)		-33 (33MHz)		-40 (40MHz)		UNITS
					MIN	MAX	MIN	MAX	MIN	MAX	
Output Rise Time	t_{OR}		7, 8	$-55 \le T_A \le 125$	-	5	-	5	-	3	ns
Output Fall Time	t_{OF}		7, 8	$-55 \le T_A \le 125$	-	5	-	5	-	3	ns

NOTES:

7. Parameters listed in Table 3 are controlled via design or process parameters and are not directly tested. These parameters are characterized upon initial design and after major process and/or design changes.
8. Loading is as specified in the test load circuit with C_L = 40pF.

TABLE 4. ELECTRICAL TEST REQUIREMENTS

CONFORMANCE GROUPS	METHOD	SUBGROUPS
Initial Test	100%/5004	-
Interim Test	100%/5004	-
PDA	100%	1
Final Test	100%	2, 3, 8A, 8B, 10, 11
Group A	-	1, 2, 3, 7, 8A, 8B, 9, 10, 11
Groups C and D	Samples/5005	1, 7, 9

Burn-In Circuit

	1	2	3	4	5	6	7	8	9	10	11
L		$\overline{OEH}$	DLY BLK	START $\overline{OUT}$	V_{CC}	BLOCK $\overline{DONE}$	GND	OUT1	OUT2	NC	
K	NC	NC	$\overline{OEL}$	START $\overline{IN}$	ADD $\overline{VAL}$	$\overline{BUSY}$	$\overline{DONE}$	OUTO	V_{CC}	NC	OUT3
J	$\overline{RST}$	V_{CC}								GND	OUT4
H	CLK	GND								OUT5	V_{CC}
G	$\overline{CS}$	A0								OUT6	OUT7
F	$\overline{WR}$	GND								GND	OUT8
E	D6	D5								OUT9	V_{CC}
D	D4	D3								OUT10	OUT11
C	D2	D1								GND	OUT12
B	D0	NC	OUT22	OUT21	GND	OUT18	OUT17	GND	OUT14	NC	NC
A		GND	OUT23	V_{CC}	OUT20	OUT19	V_{CC}	OUT16	OUT15	OUT13	

PGA PIN	PIN NAME	BURN-IN SIGNAL	PGA PIN	PIN NAME	BURN-IN SIGNAL	PGA PIN	PIN NAME	BURN-IN SIGNAL	PGA PIN	PIN NAME	BURN-IN SIGNAL
A2	GND	GND	B9	OUT14	$V_{CC}/2$	F11	OUT8	$V_{CC}/2$	K6	BUSYB	$V_{CC}/2$
A3	OUT23	$V_{CC}/2$	C1	D2	F10	G1	CSB	F5	K7	DONEB	$V_{CC}/2$
A4	V_{CC}	V_{CC}	C2	D1	F9	G2	A0	F6	K8	OUT0	$V_{CC}/2$
A5	OUT20	$V_{CC}/2$	C10	GND	GND	G10	OUT6	$V_{CC}/2$	K9	V_{CC}	V_{CC}
A6	OUT19	$V_{CC}/2$	C11	OUT12	$V_{CC}/2$	G11	OUT7	$V_{CC}/2$	K11	OUT3	$V_{CC}/2$
A7	V_{CC}	V_{CC}	D1	D4	F12	H1	CLK	F0	L2	OEHB	F13
A8	OUT16	$V_{CC}/2$	D2	D3	F11	H2	GND	GND	L3	DLYBLK	F11
A9	OUT15	$V_{CC}/2$	D10	OUT10	$V_{CC}/2$	H10	OUTS	$V_{CC}/2$	L4	STARTOUTB	$V_{CC}/2$
A10	OUT13	$V_{CC}/2$	D11	OUT11	$V_{CC}/2$	H11	V_{CC}	V_{CC}	LS	V_{CC}	V_{CC}
B1	D0	F8	E1	D6	F7	J1	RSTB	F14	L6	BLOCKDONEB	$V_{CC}/2$
B3	OUT22	$V_{CC}/2$	E2	D5	F13	J2	V_{CC}	V_{CC}	L7	GND	GND
B4	OUT21	$V_{CC}/2$	E10	OUT9	$V_{CC}/2$	J10	GND	GND	L8	OUT1	$V_{CC}/2$
B5	GND	GND	E11	V_{CC}	V_{CC}	J1 1	OUT4	$V_{CC}/2$	L9	OUT2	$V_{CC}/2$
B6	OUT18	$V_{CC}/2$	F1	WRB	F4	K3	OELB	F12			
B7	OUT17	$V_{CC}/2$	F2	GND	GND	K4	START1NB	F6			
B8	GND	GND	F10	GND	GND	K5	ADVALB	$V_{CC}/2$			

NOTES:

9. $V_{CC}/2$ (2.7V ±10%) used for outputs only.
10. 47Ω (±20%) resistor connected to all pins except V_{CC} and GND.
11. V_{CC} = 5.5 ±0.5V.
12. 0.1µF (min) capacitor between V_{CC} and GND per position.
13. F0 = 100kHz ±10%, F1 = F0/2, F2 = F1/2....., F11 = F10/2, 40% -60% Duty Cycle.
14. Input voltage limits: V_{IL} = 0.8V max., V_{IH} = 4.5V ±10%.

Die Characteristics

DIE DIMENSIONS:

186 mils x 222 mils x 19 ±1mils

METALLIZATION:

Type: Si - Al or Si-Al-Cu
Thickness: 8kÅ

GLASSIVATION:

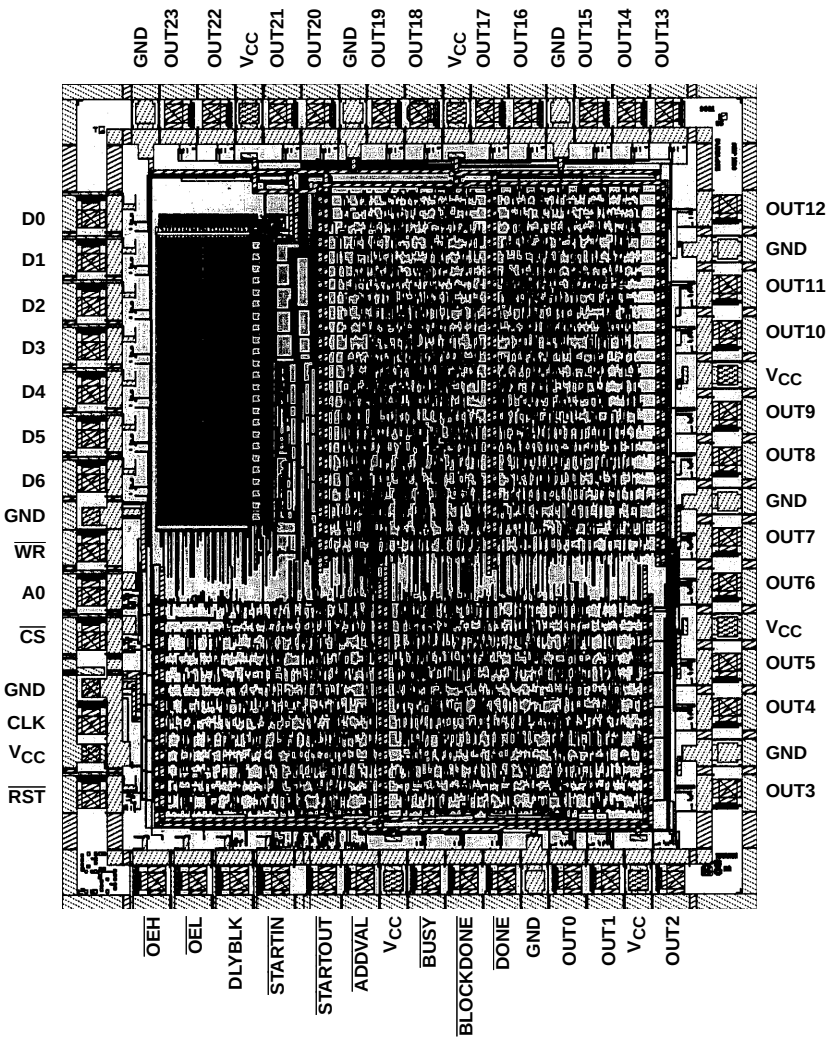
Type: Nitrox
Thickness: 10kÅ

WORST CASE CURRENT DENSITY:

$1.8 \times 10^5 A/cm^2$

Metallization Mask Layout

HSP45240/883



All Intersil semiconductor products are manufactured, assembled and tested under **ISO9000** quality systems certification.